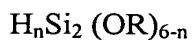


IN THE CLAIMS

Please amend the claims as follows:

Claims 1-5 (Canceled).

Claim 6 (New): A method for producing a silicon oxide film comprising the step of forming a silicon oxide film by thermochemical vapor-phase deposition at the pressure in the range from 0.01mmHg to 2 atm using a silane compound of the formula



wherein

R is an alkyl group of carbon number from 1 to 6, and n is an integer from 0 to 5 and a diluting gas.

Claim 7 (New): The method for producing a silicon oxide film according to Claim 1, wherein said silicon oxide film is formed by plasma chemical vapor-phase deposition.

Claim 8 (New): The method for producing a silicon oxide film according to Claim 1, wherein ozone is used as an oxidizing agent.

Claim 9 (New): The method for producing a silicon oxide film according to Claim 1, wherein the deposition temperature is controlled to the range from 200 to 500°C.

Claim 10 (New): A method for manufacturing a semiconductor device comprising the step of depositing an insulating film comprising a silicon oxide film of Claim 1.